

## N0132S Process Geometry

### Features

- Low Noise: 1.2 nV/VHz Typical
- Typical Input Capacitance: 13pF
- Typical Breakdown Voltage: -45V
- High Input Impedance
- Small Die: 518um X 518um X 203um
- Bond Pads: 90um X 90um
- Substrate Connected to Gate
- Au Back-Side Finish

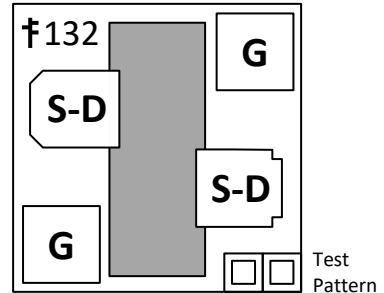
### Applications

- Low Noise Amplifier
- Audio Amplifiers
- Mid to High-Gain Applications
- Matched Pair Applications
- Custom Part Options

### Description

The InterFET N0132S Geometry is ideal for low noise high gain applications. Similar features to the N0132L Geometry with higher BV and lower input capacitance.

Geometry Top View



### Standard Parts

- 2N4391, 2N4392, 2N4393
- 2N3970, 2N3971, 2N3972
- 2N4856/A, 2N4857/A, 2N4858/A
- 2N4859/A, 2N4860/A, 2N4861/A
- J111, J112, J113
- IFN113

### Product Summary

Parameters	Min	Typ	Max	Unit
BV <sub>GSS</sub> Gate to Source Breakdown Voltage	-35	-45		V
I <sub>DSS</sub> Drain to Source Saturation Current	5		150	mA
V <sub>GS(off)</sub> Gate to Source Cutoff Voltage	-0.5		-7	V
G <sub>FS</sub> Forward Transconductance		32		mS

### Maximum Ratings (@ T<sub>A</sub> = 25°C, Unless otherwise specified)

Parameters	Min	Typ	Max	Unit
V <sub>RGS</sub> Reverse Gate to Source or Drain Voltage	-35	-45		V
I <sub>FG</sub> Continuous Forward Gate Current			10	mA
T <sub>J</sub> Operating Junction Temperature	-55		150	°C
T <sub>STG</sub> Storage Temperature	-65		175	°C



**Disclaimer:** It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.

## Electrical Characteristics

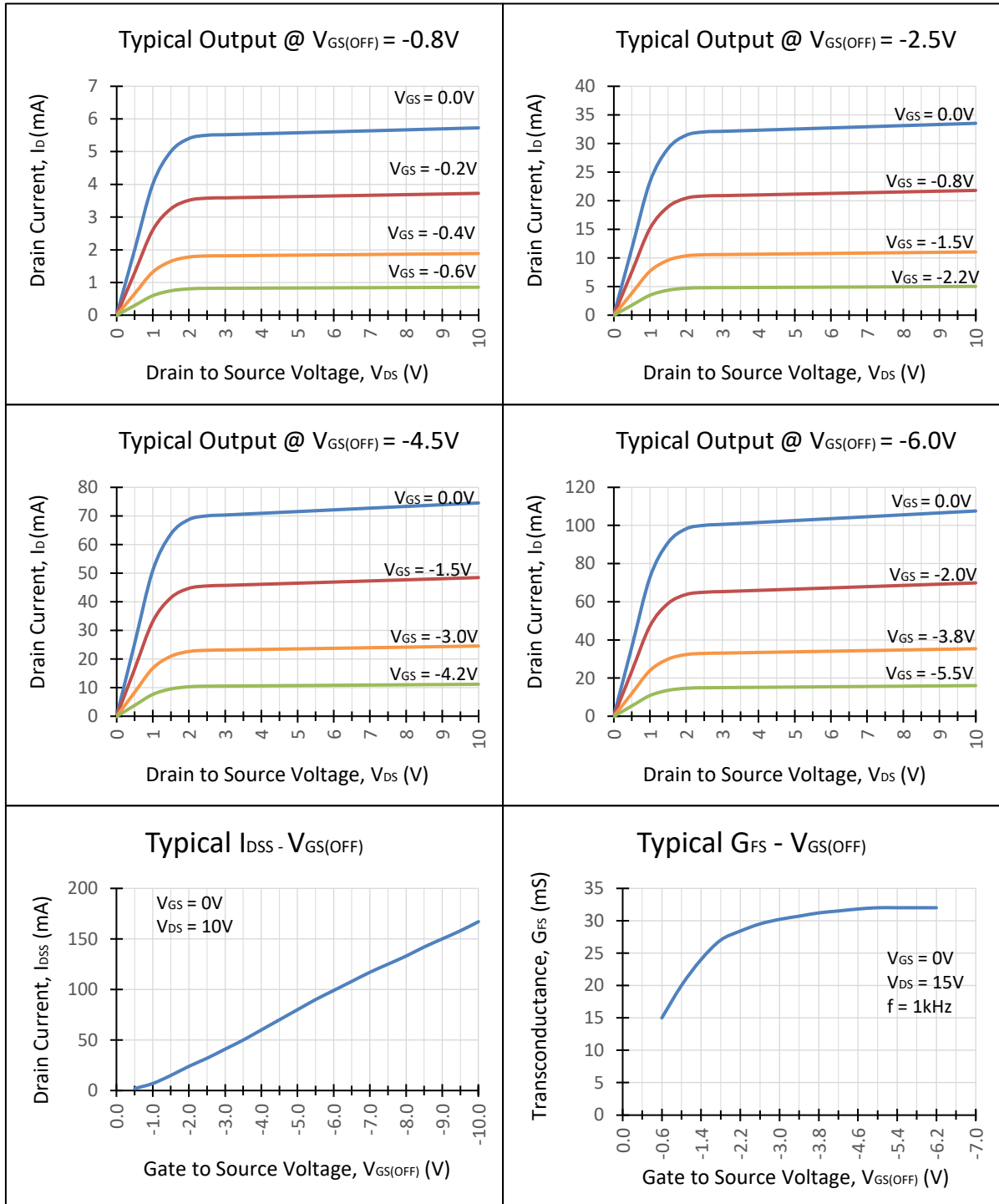
### Static Characteristics (@ TA = 25°C, Unless otherwise specified)

Parameters	Conditions	Min	Typ	Max	Unit
BV <sub>GSS</sub> Gate to Source Breakdown Voltage	I <sub>G</sub> = -1μA, V <sub>DS</sub> = 0V	-35	-45		V
I <sub>GSS</sub> Gate to Source Reverse Current	V <sub>GS</sub> = -10V, V <sub>DS</sub> = 0V		-50	-100	pA
V <sub>GS(OFF)</sub> Gate to Source Cutoff Voltage	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1nA	-0.5		-7	V
I <sub>DSS</sub> Drain to Source Saturation Current	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V	5		150	mA

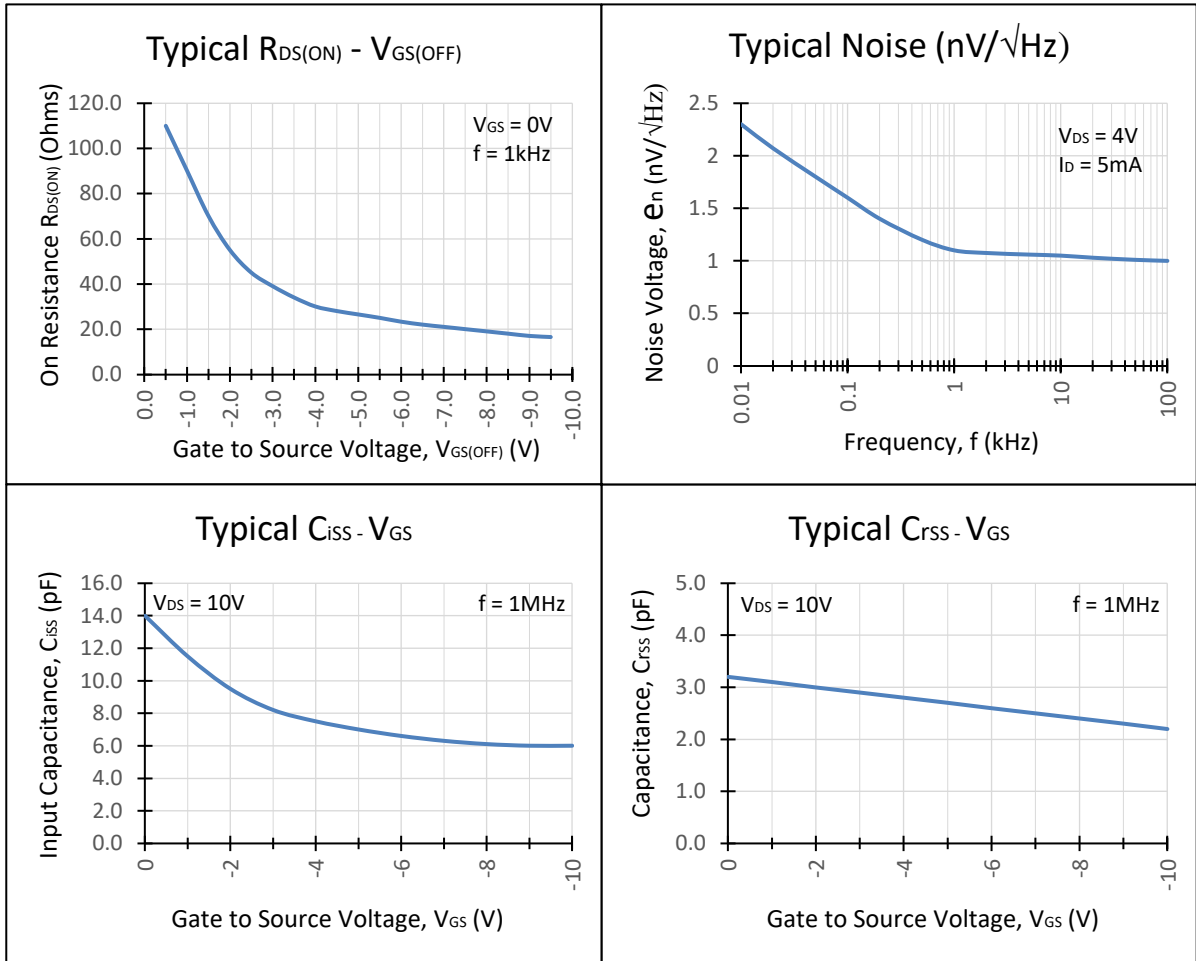
### Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

Parameters	Conditions	Min	Typ	Max	Unit
G <sub>FS</sub> Forward Transconductance	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0 V, f = 1kHz		32		mS
C <sub>iss</sub> Input Capacitance	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0 V, f = 1MHz		13		pF
C <sub>rss</sub> Reverse Transfer Capacitance	V <sub>DS</sub> = 0V, V <sub>GS</sub> = -10 V, f = 1MHz		3.0		pF
e <sub>n</sub> Noise Voltage	V <sub>DS</sub> = 4V, I <sub>D</sub> = 5mA, f = 1kHz		1.2		nV/√Hz

## Typical N0132S Characteristics

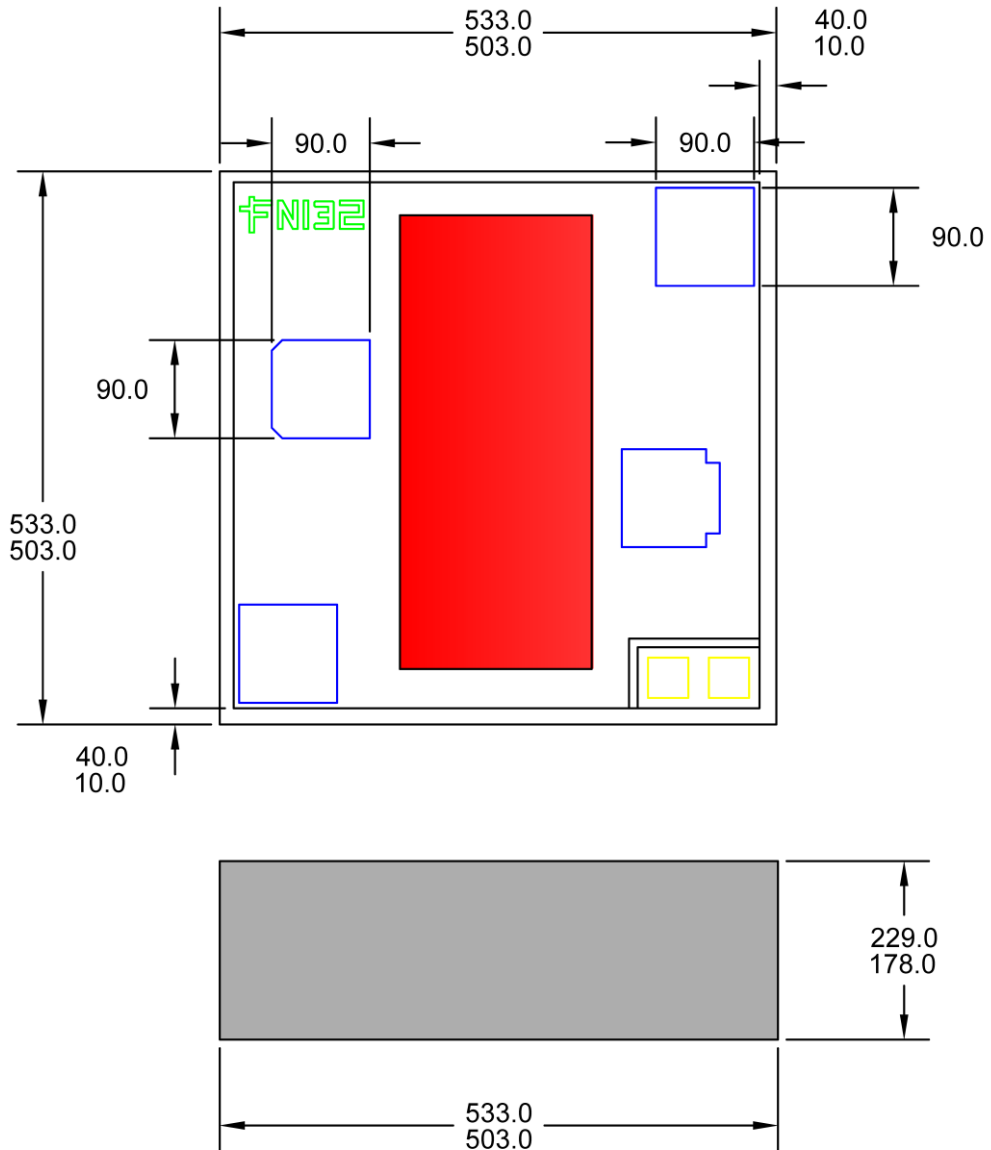


**Typical N0132S Characteristics (Continued)**



## N0132S Die Geometry Mechanical

### Raw Die Dimensions



1. All linear dimensions are in micrometers.